Improved Anisotropic Strain Control in Semipolar Nitride Devices
Tech ID: 25606 / UC Case 2009-743-0

BRIEF DESCRIPTION
A method to control the anisotropy of strain in semipolar nitride-based active layers of optoelectronic devices while maintaining high device performance and efficiency.

BACKGROUND
Nitride-based devices are typically grown coherently because dislocations can cause poor device performance. The presence of strain in quantum wells (QWs) can modulate the band structure of QWs (polarization of spontaneous emission and gain). Generally, strain in semipolar nitride epitaxial layers is anisotropic due to the different lattice parameters. This strain-anisotropy is automatically determined by the difference of lattice constant between a considered epitaxial layer and the substrate on which the considered layer is coherently grown. Therefore, techniques are needed to control the anisotropy of strain in QWs.

DESCRIPTION
UC Santa Barbara researchers have created a method to control the anisotropy of strain in semipolar nitride-based active layers of optoelectronic devices while maintaining high device performance and efficiency. Using this method, misfit dislocations may be restricted to regions located far from device layers.

ADVANTAGES
▶ Controlled anisotropic strain
▶ High efficiency
▶ Improved device performance
▶ Increased device yield
▶ Reduction of dislocations in active devices

APPLICATIONS
▶ LEDs
▶ Laser diodes (LDs)

PATENT STATUS
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<td>8,481,991</td>
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ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- Etching Technique for the Fabrication of Thin (Al, In, Ga)N Layers
- Lateral Growth Method for Defect Reduction of Semipolar Nitride Films
- Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation
- III-Nitride-Based Vertical Cavity Surface Emitting Laser (VCSEL) with a Dielectric P-Side Lens
- Aluminum-cladding-free Nonpolar III-Nitride LEDs and LDs
- Low-Cost Zinc Oxide for High-Power-Output, GaN-Based LEDs (UC Case 2010-183)
- Defect Reduction in GaN films using in-situ SiNx Nanomask
- Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
- Low TemperatureDeposition of Magnesium Doped Nitride Films
- Transparent Mirrorless (TML) LEDs
- Improved GaN Substrates Prepared with Ammonothermal Growth
- Optimization of Laser Bar Orientation for Nonpolar Laser Diodes
- Method for Enhancing Growth of Semipolar Nitride Devices
- Ultraviolet Laser Diode on Nano-Porous AlGaN template
- Improved Reliability & Enhanced Performance of III-Nitride Tunnel Junction Optoelectronic Devices
- Growth of Polyhedron-Shaped Gallium Nitride Bulk Crystals
- Nonpolar III-Nitride LEDs With Long Wavelength Emission
- Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices
- Growth of High-Quality, Thick, Non-Polar M-Plane GaN Films
- High-Efficiency, Mirrorless Non-Polar and Semi-Polar Light Emitting Devices
- Method for Growing High-Quality Group III-Nitride Crystals
- Controlled Photoelectrochemical (PEC) Etching by Modification of Local Electrochemical Potential of Semiconductor Crystals
- Oxyfluoride Phosphors for Use in White Light LEDs
- Technique for the Nitride Growth of Semipolar Thin Films, Heterostructures, and Semiconductor Devices
- (In,Ga,Al)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- Group III-N Light Emitting Devices Enhanced By Stress From Post-Growth Deposited Films
- Thermally Stable, Laser-Driven White Lighting Device
- MOCVD Growth of Planar Non-Polar M-Plane Gallium Nitride
- Reduced Dislocation Density of Non-Polar GaN Grown by Hydride Vapor Phase Epitaxy
- Methods for Fabricating III-Nitride Tunnel Junction Devices
- Low-Droop LED Structure on GaN Semi-polar Substrates
- Contact Architectures for Tunnel Junction Devices
- Semi-polar LED/LD Devices on Relaxed Template with Misfit Dislocation at Hetero-interface
- Semipolar-Based Yellow, Green, Blue LEDs with Improved Performance
- III-Nitride-Based Devices Grown On Thin Template On Thermally Decomposed Material
- Growth of Semipolar III-V Nitride Films with Lower Defect Density
- III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
- Tunable White Light Based on Polarization-Sensitive LEDs
- Cleaved Facet Edge-Emitting Laser Diodes Grown on Semipolar GaN
- Growth of High-Performance M-plane GaN Optical Devices
- Packaging Technique for the Fabrication of Polarized Light Emitting Diodes
Novel Multilayer Structure for High-Efficiency UV and Far-UV Light-Emitting Devices
III-V Nitride Device Structures on Patterned Substrates
Method for Increasing GaN Substrate Area in Nitride Devices
High-Intensity Solid State White Laser Diode
Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
Growth of Planar, Non-Polar, A-Plane GaN by Hydride Vapor Phase Epitaxy
GaN-Based Thermoelectric Device for Micro-Power Generation
Limiting Strain-Relaxation in III-Nitride Heterostructures by Substrate Patterning
LED Device Structures with Minimized Light Re-Absorption
Growth of Planar Semi-Polar Gallium Nitride
High-Efficiency and High-Power III-Nitride Devices Grown on or Above a Strain Relaxed Template
Nonpolar (Al, B, In, Ga)N Quantum Well Design
UV Optoelectronic Devices Based on Nonpolar and Semi-polar AlInN and AlInGaN Alloys
Defect Reduction of Non-Polar and Semi-Polar III-Nitrides
III-Nitride Based VCSEL with Curved Mirror on P-Side of the Aperture
Enhancing Growth of Semipolar (Al,In,Ga,B)N Films via MOCVD